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Discrete POWER & Signal **Technologies** 

# **MPS6531**

FAIRCHILD SEMICONDUCTOR TM

## **MPS6531**



### NPN General Purpose Amplifier

This device is designed for use as a medium power amplifier and switch requiring collector currents to 500 mA. Sourced from Process 19. See PN2222A for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
$V_{\text{EBO}}$	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	1.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted					
Symbol	Characteristic	Мах	Units		
		MPS6531			
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C		
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	83.3	°C/W		
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W		

# NPN General Purpose Amplifier (continued)

HubbleDefinitionDefinitionDefinitionHubbleHubbleHubble $V_{(BR)CBO}$ Collector-Base Breakdown Voltage $I_c = 10 \ \mu A, I_E = 0$ 60V $V_{(BR)EBO}$ Emitter-Base Breakdown Voltage $I_E = 10 \ \mu A, I_C = 0$ 5.0V $I_{CBO}$ Collector Cutoff Current $V_{CB} = 40 \ V, I_E = 0$ $V_{CB} = 40 \ V, I_E = 0, T_A = 60 \ ^\circ C$ 50nON CHARACTERISTICS*NFEDC Current Gain $V_{CE} = 1.0 \ V, I_C = 10 \ mA$ $V_{CE} = 1.0 \ V, I_C = 500 \ mA$ 60 $90$ $50$ VCE(sat)Collector-Emitter Saturation Voltage $I_C = 100 \ mA, I_B = 10 \ mA$ 0.3 $V_{BE(sat)}$ Base-Emitter Saturation Voltage $I_C = 100 \ mA, I_B = 10 \ mA$ 1.0	Collector-Emitter Breakdown Voltage* $I_c = 10 \text{ mA}, I_B = 0$ 40VCollector-Base Breakdown Voltage $I_c = 10 \mu A, I_E = 0$ 60VEmitter-Base Breakdown Voltage $I_E = 10 \mu A, I_C = 0$ 5.0V
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V <sub>CB</sub> = 40 V, I <sub>E</sub> = 0, T <sub>A</sub> = 60 °C     2.0 $\mu$ ON CHARACTERISTICS*     V <sub>CE</sub> = 1.0 V, I <sub>C</sub> = 10 mA     60     270       h <sub>FE</sub> DC Current Gain     V <sub>CE</sub> = 1.0 V, I <sub>C</sub> = 100 mA     90     270       V <sub>CE</sub> (sat)     Collector-Emitter Saturation Voltage     I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA     0.3     N       V <sub>BE</sub> (sat)     Base-Emitter Saturation Voltage     I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA     1.0     N	
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$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	
$\label{eq:V_cE} V_{CE} = 1.0 \text{ V}, \text{ I}_{C} = 100 \text{ mA} \qquad 90 \qquad 270 \\ V_{CE} = 10 \text{ V}, \text{ I}_{C} = 500 \text{ mA} \qquad 50 \qquad 50 \qquad 0.3 $	
$V_{CE}$ = 10 V, $I_C$ = 500 mA50 $V_{CE(sat)}$ Collector-Emitter Saturation Voltage $I_C$ = 100 mA, $I_B$ = 10 mA0.3 $V_{BE(sat)}$ Base-Emitter Saturation Voltage $I_C$ = 100 mA, $I_B$ = 10 mA1.0	
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage $I_c = 100 \text{ mA}, I_B = 10 \text{ mA}$ 0.3V $V_{BE(sat)}$ Base-Emitter Saturation Voltage $I_c = 100 \text{ mA}, I_B = 10 \text{ mA}$ 1.0V	
$V_{BE(sat)}$ Base-Emitter Saturation Voltage I <sub>c</sub> = 100 mA, I <sub>B</sub> = 10 mA 1.0 V	Collector-Emitter Saturation Voltage $I_c = 100 \text{ mA}$ $I_B = 10 \text{ mA}$ 0.3 V
	Base-Emitter Saturation Voltage $I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$ 1.0 V
SMALL SIGNAL CHARACTERISTICS	
	NAL CHARACTERISTICS
$C_{ob}$ Output Capacitance $V_{CB} = 10 V$ , f = 100 kHz 5.0 p	Dutput Capacitance $V_{CB} = 10 \text{ V}, \text{ f} = 100 \text{ kHz}$ 5.0 pl
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%	

MPS6531



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